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November 2013

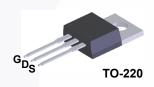
FQP32N20C / FQPF32N20C N-Channel QFET[®] MOSFET 200 V, 28 A, 82 mΩ

Features

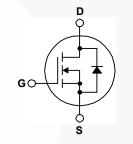
- 28 A, 200 V, ${\sf R}_{{\sf DS}({\sf on})}$ = 82 m Ω (Max.) @ ${\sf V}_{{\sf GS}}$ = 10 V, ${\sf I}_{{\sf D}}$ = 14 A
- Low Gate Charge (Typ. 82.5 nC)
- Low Crss (Typ. 185 pF)
- 100% Avalanche Tested

Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.







MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Parameter			FQP32N20C	FQPF32N20C	Unit
Drain to Source Voltage			200		V
Drain Current	-Continuous (T _C = 25 ^o C)	-Continuous (T _C = 25 ^o C) -Continuous (T _C = 100 ^o C)		28.0 *	А
Drain Current	-Continuous (T _C = 100 ^o C)			17.8 *	А
Drain Current	- Pulsed	(Note 1)	112	112 *	А
Gate to Source Voltage			± 30		V
Single Pulsed Avalanche Energy		(Note 2)	955		mJ
Avalanche Current		(Note 1)	28.0		А
Repetitive Avalanche Energy		(Note 1)	15.6		mJ
Peak Diode Recovery dv/dt		(Note 3)	5.5		V/ns
Dower Dissinction	(T _C = 25°C)		156	50	W
Power Dissipation	- Derate above 25°C		1.25	0.4	W/°C
Operating and Storage Temperature Range		-55 to +150		°C	
Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds			300		°C
	Drain Current Drain Current Gate to Source Voltage Single Pulsed Avalanch Avalanche Current Repetitive Avalanche E Peak Diode Recovery c Power Dissipation Operating and Storage Maximum Lead Temper	$\begin{tabular}{ c c c c } \hline Drain to Source Voltage & -Continuous (T_C = 25^\circ C) & -Continuous (T_C = 100^\circ C) \\ \hline Drain Current & -Pulsed \\ \hline Drain Current & -Pulsed \\ \hline Gate to Source Voltage & Single Pulsed Avalanche Energy & Avalanche Current \\ \hline Repetitive Avalanche Energy & Peak Diode Recovery dv/dt & Power Dissipation & (T_C = 25^\circ C) & -Derate above 25^\circ C \\ \hline Operating and Storage Temperature Range & Maximum Lead Temperature for Soldering Purpose, \\ \hline \end{tabular}$	$\begin{tabular}{ c c c c } \hline Drain to Source Voltage & -Continuous (T_C = 25^{\circ}C) & -Continuous (T_C = 100^{\circ}C) & -Pulsed & (Note 1) & -Pulsed & (Note 2) & -Pulsed & (Note 2) & -Pulsed & -Avalanche Energy & (Note 2) & -Avalanche Current & (Note 1) & -Avalanche Current & (Note 1) & -Peak Diode Recovery dv/dt & (Note 3) & -Peak Diode Recovery dv/dt & (Note 3) & -Peak Diode Recovery dv/dt & (Note 3) & -Peate above 25^{\circ}C & -Perate above 25^{\circ}C $	Drain to Source Voltage24Drain Current-Continuous ($T_C = 25^{\circ}C$) -Continuous ($T_C = 100^{\circ}C$)28.0Drain Current-Pulsed(Note 1)Drain Current-Pulsed(Note 1)Gate to Source Voltage±Single Pulsed Avalanche Energy(Note 2)Avalanche Current(Note 1)Repetitive Avalanche Energy(Note 1)Peak Diode Recovery dv/dt(Note 3)Power Dissipation($T_C = 25^{\circ}C$) - Derate above $25^{\circ}C$ 156Operating and Storage Temperature Range-55 toMaximum Lead Temperature for Soldering Purpose,30	Drain to Source Voltage200Drain Current-Continuous ($T_C = 25^{\circ}C$) -Continuous ($T_C = 100^{\circ}C$)28.0Drain Current-Pulsed(Note 1)Drain Current-Pulsed(Note 1)Gate to Source Voltage ± 30 Single Pulsed Avalanche Energy(Note 2)Avalanche Current(Note 1)Repetitive Avalanche Energy(Note 1)Repetitive Avalanche Energy(Note 1)Peak Diode Recovery dv/dt(Note 3) $C_C = 25^{\circ}C$) - Derate above $25^{\circ}C$ 156Power Dissipation $(T_C = 25^{\circ}C)$ - Derate above $25^{\circ}C$ Operating and Storage Temperature Range-55 to +150Maximum Lead Temperature for Soldering Purpose,300

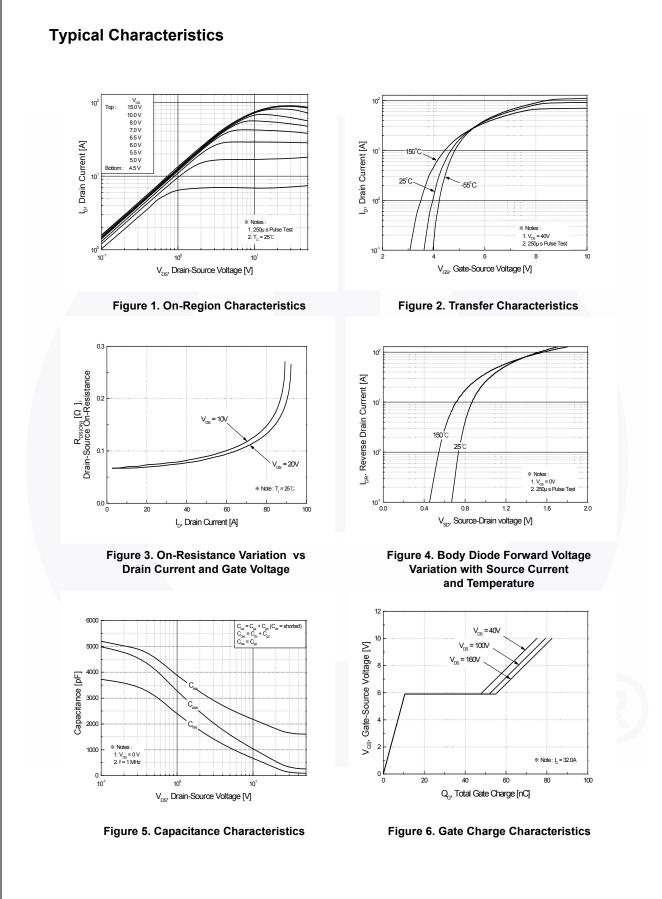
Thermal Characteristics

Symbol	Parameter	FQP32N20C	FQPF32N20C	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max	0.8	2.51	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient, Max	62.5	62.5	°C/W

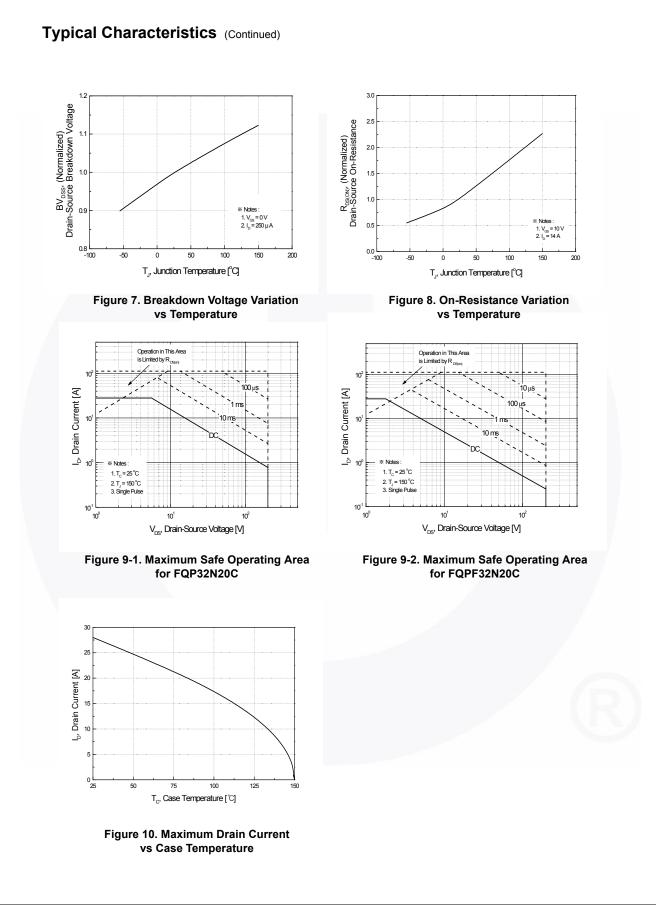
Device MarkingDeviceFQP32N20CFQP32N20CFQPF32N20CFQPF32N20C		Device	Package	Ree	l Size	Tape Width	n Qu	antity	
		FQP32N20C			ube	N/A	50	50 units	
		TO-220F Tu		ube	N/A	50 units			
lectri	cal Characte	eristics T _C = 25°C ur	nless otherwise noted.						
Symbol	Pa	arameter	Test Conditions	6	Min	Тур	Max	Unit	
Off Cha	racteristics								
BV _{DSS}	Drain-Source Bre	eakdown Voltage	V _{GS} = 0 V, I _D = 250 μA		200			V	
ΔBV _{DSS} / ΔT _J		ige Temperature Coeffi-	$I_D = 250 \mu$ A, Referenced to 25°C			0.24		V/°C	
		D 1 0 1	V _{DS} = 200 V, V _{GS} = 0 V				10	μA	
IDSS	Zero Gate Voltag	je Drain Current	$V_{DS} = 160 \text{ V}, \text{ T}_{C} = 125^{\circ}\text{C}$				100	μA	
I _{GSSF}	Gate-Body Leak	age Current, Forward	V_{GS} = 30 V, V_{DS} = 0 V				100	nA	
I _{GSSR}	Gate-Body Leak	age Current, Reverse	V_{GS} = -30 V, V_{DS} = 0 V				-100	nA	
On Cha	racteristics								
V _{GS(th)}	Gate Threshold	Voltage	V_{DS} = V_{GS} , I_D = 250 μ A		2.0		4.0	V	
R _{DS(on)}	Static Drain-Sour On-Resistance	rce	V _{GS} = 10 V, I _D = 14 A			0.068	0.082	Ω	
9 _{FS}	Forward Transco	onductance	V _{DS} = 40 V, I _D = 14 A			20		S	
Dvnam	ic Characteris	tics							
C _{iss}	Input Capacitance		N 05 Y Y 0 Y			1700	2220	pF	
C _{oss}	Output Capacita		V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz			400	520	pF	
C _{rss}	Reverse Transfe					185	245	pF	
	1								
	ng Characteri								
t _{d(on)}	Turn-On Delay T		V_{DD} = 100 V, I _D = 32 A, R _G = 25 Ω			25	60	ns	
t _r	Turn-On Rise Tir					270	550	ns	
t _{d(off)}	Turn-Off Delay T					245	500	ns	
t _f	Turn-Off Fall Tim	e		(Note 4)		210	430	ns	
Qg	Total Gate Charg	je	V _{DS} = 160 V, I _D = 32 A,			82.5	110	nC	
Q _{gs}	Gate-Source Cha	•	V _{GS} = 10 V			10.5		nC	
Q _{gd}	Gate-Drain Char	ge		(Note 4)		44.5		nC	
Drain-S	ource Diode (Characteristics and	Maximum Ratings						
I _S	i	uous Drain-Source Diode					28	A	
I _{SM}	Maximum Pulsed	d Drain-Source Diode For	ward Current				112	Α	
V _{SD}		ode Forward Voltage	V _{GS} = 0 V, I _S = 28 A				1.5	V	
t _{rr}	Reverse Recove	•	V _{GS} = 0 V, I _S = 32 A,			265	-	ns	
Q _{rr}	Reverse Recove	,	dl _F / dt = 100 A/μs			2.73	-	μC	
otes:		, ,				-			

4. Essentially independent of operating temperature.

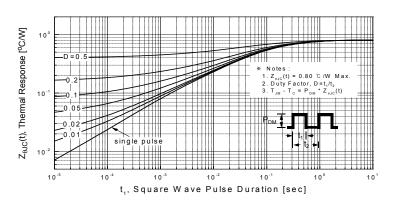
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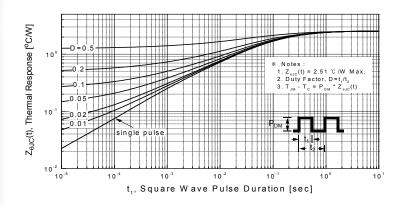
FQP32N20C / FQPF32N20C — N-Channel QFET[®] MOSFET



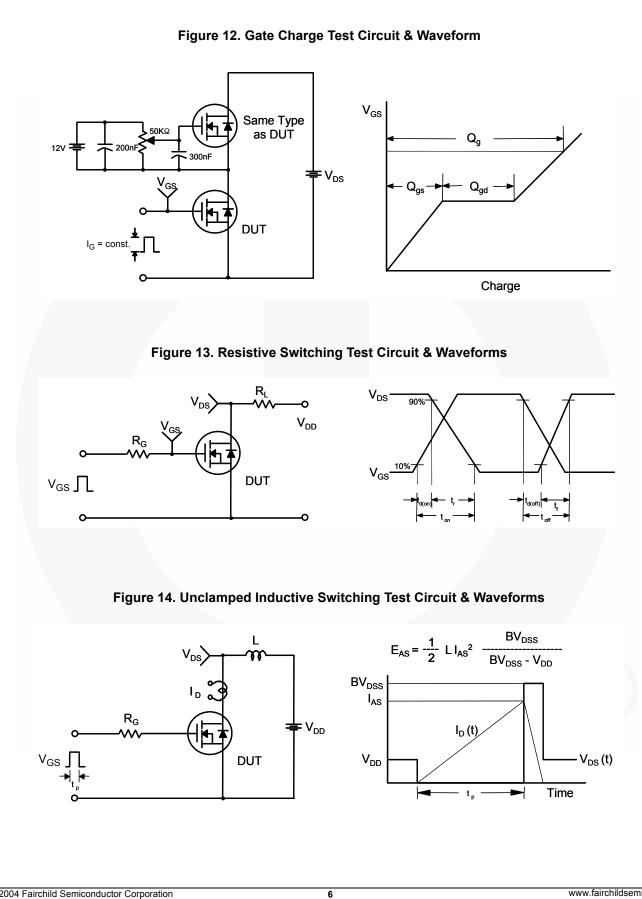
Typical Characteristics (Continued)



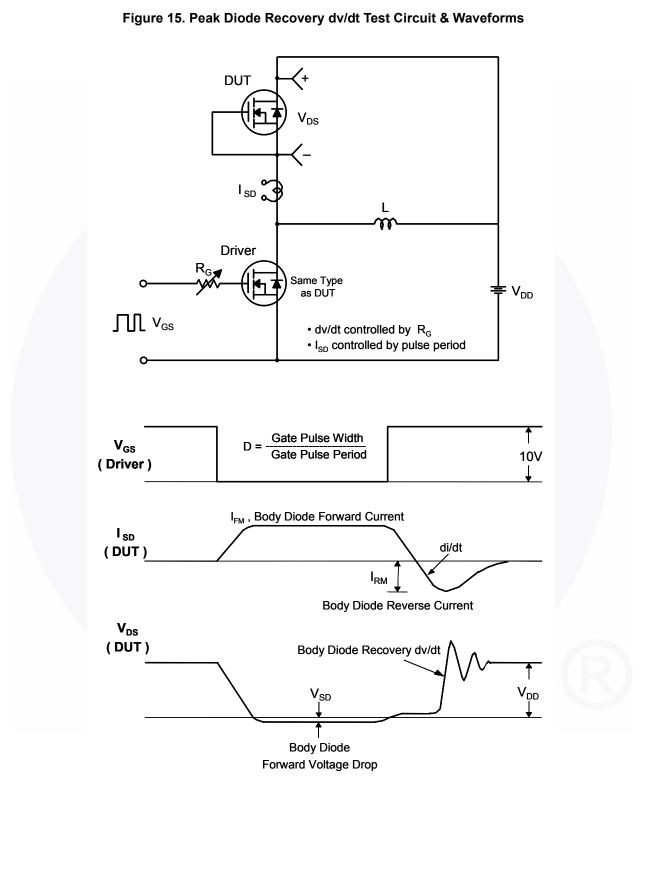




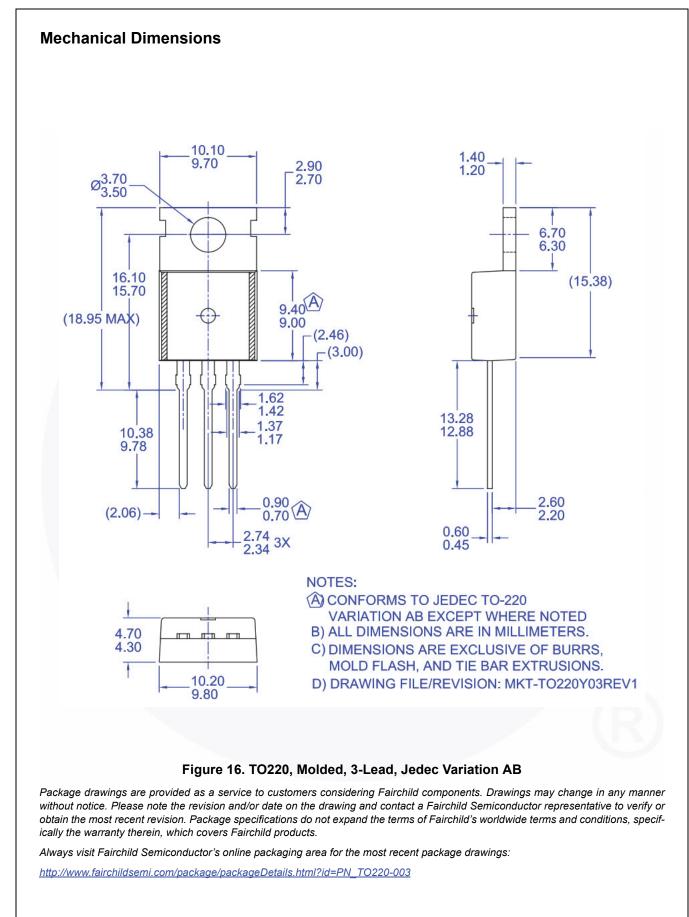


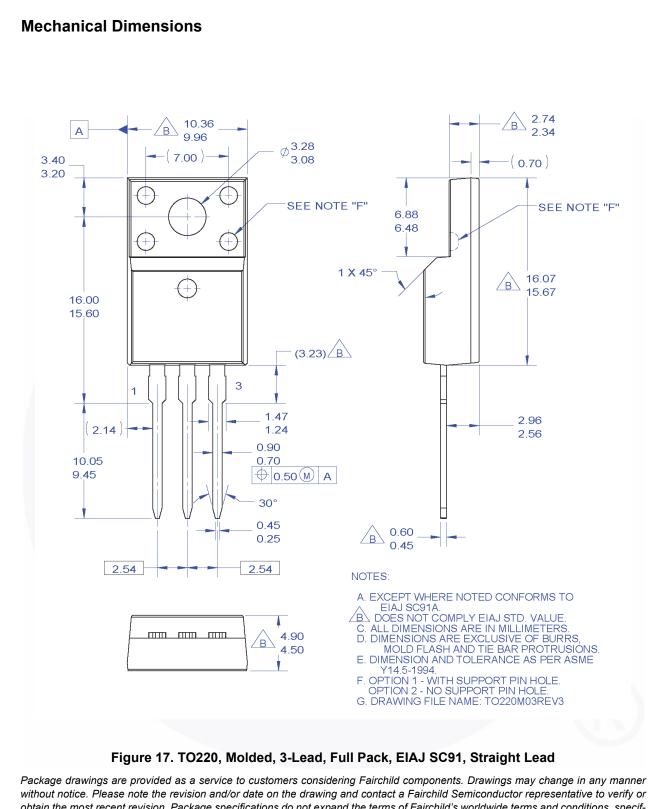


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